

LOW REFLECTIVITY TRANSPARENT CONDUCTIVE FILM AND FORMATION THEREOF

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Abstract of JP9076401

PROBLEM TO BE SOLVED: To impart antistatic electromagnetic shielding and reflection preventing functions to a transparent substrate by constituting a low reflectivity transparent conductive film of a lower film containing a tin doped indium oxide fine powder and an upper siliceous film and adding a black conductive fine powder to one of the films in specific wt. %. SOLUTION: A low reflectivity transparent conductive film is constituted of a lower film containing a tin doped indium oxide (ITO) fine powder and an upper siliceous film. At least one of the lower and upper films further contains a black conductive fine powder and, on the basis of the sum total amt. of the lower and upper films, the amt. of the tin doped indium oxide fine powder is 40-75wt. % and the amt. of the black conductive fine powder is 1-25wt. % and a low reflectivity electromagnetic wave shielding colorless transparent conductive film is formed on the surface of a transparent substrate. The average primary particle size of the ITO fine powder is 0.2 μ m or less, pref., 0.1 μ m or less in order not to obstruct transparency.